



Form PTO-1449 <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> <i>(Use several sheets if necessary)</i>	Docket Number 299002052200	Application Number 09/786,977
	Applicant Koji TAKAHASHI and Hidenori KAWANISHI	
	Filing Date June 7, 2001	Group Art Unit 2822
	Mailing Date January 28, 2003	

**U.S. PATENT DOCUMENTS**

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate
J.B.	1.	12/24/96	5,587,014	Iyechika et al.			

**FOREIGN PATENT DOCUMENTS**

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO
J.B.	2.	1/22/99	JP 11-017284	Japan			Abstract

**OTHER DOCUMENTS**

*(including author, title, Date, Pertinent Pages, Etc.)*

Examiner Initials	Ref. No.	Title
J.B.	3.	Mendoza-Diaz, G. et al. (1997). "Feasibility of the Synthesis of AlAsN and GaAsN Films by Plasma-source Molecular-beam Epitaxy," <i>Journal of Crystal Growth</i> 178(1-2):45-55.
	4.	Qui, Y. et al. (1998). "Metalorganic Molecular Beam Epitaxy of GaAsN with Dimethylhydrazine," <i>Applied Physics Letters</i> 72(16)
	5.	Sakai, Shiro et al. (1998). "Growth of InNAs on GaAs(1 0 0) Substrates by Molecular-beam Epitaxy," <i>Journal of Crystal Growth</i> 189/190:471-475
J.B.	6.	Uesugi, Katsuhiko et al. (1998). "Metalorganic Molecular Beam Epitaxy of GaNAs Alloys on (0 0 1)GaAs," <i>Journal of Crystal Growth</i> 189/190:490-495

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EXAMINER: <u>Jamie L. Brophy</u>	DATE CONSIDERED: <u>June 17, 2003</u>
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